

Abstract Of The Invention

The invention includes a process for manufacturing an integrated circuit, comprising providing a substrate comprising a dielectric layer over a conductive material,
5 depositing a hardmask over the dielectric layer, applying a first photoresist over the hardmask and photodefining a trench, etching the hard mask and partially etching the dielectric to form a trench having a bottom, stripping the photoresist, applying a second photoresist and photodefining a slit across the trench, selectively etching the dielectric from the bottom of the trench down to the underlying conductive material. Both the
10 hardmask and the second photoresist are used as a mask. Later, a connection to the underlying metal is formed and integrated circuits made thereby.

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